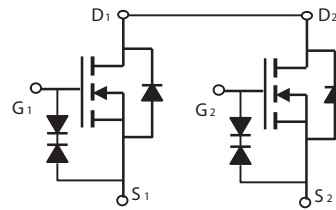
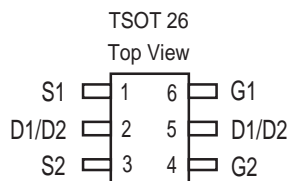


**Dual N-Channel Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
20V	8A	14.5 @ V _{GS} =4.5V
		15 @ V _{GS} =4.0V
		15.5 @ V _{GS} =3.7V
		18 @ V _{GS} =3.1V
		22 @ V _{GS} =2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

**ABSOLUTE MAXIMUM RATINGS** (T_A=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D	Drain Current-Continuous ^a	T _A =25°C	8
		T _A =70°C	6.4
I _{DM}	-Pulsed ^b	50	A
P _D	Maximum Power Dissipation ^a	T _A =25°C	1.25
		T _A =70°C	0.8
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	100	°C/W
------------------	--	-----	------

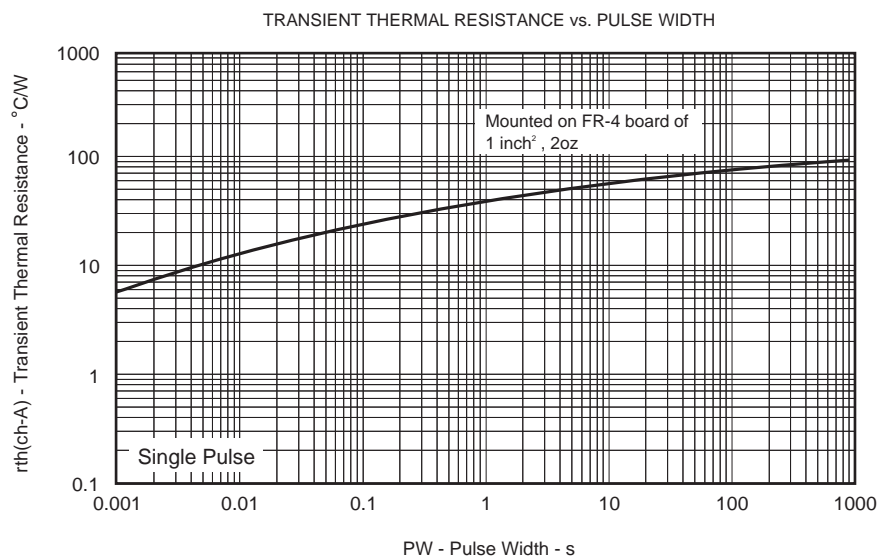
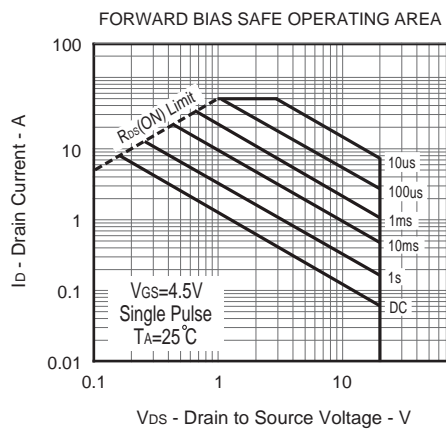
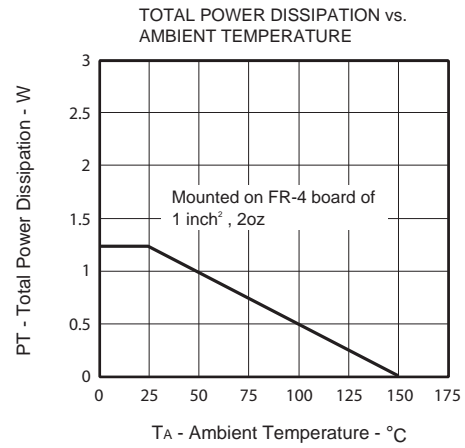
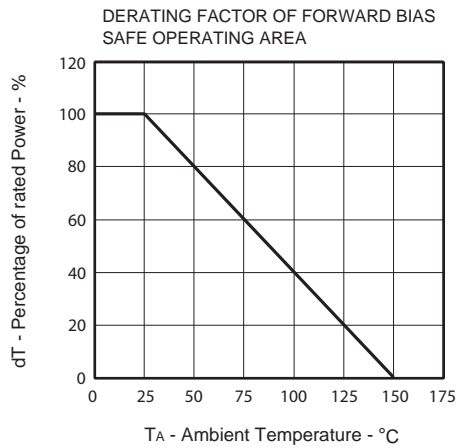
STS8212

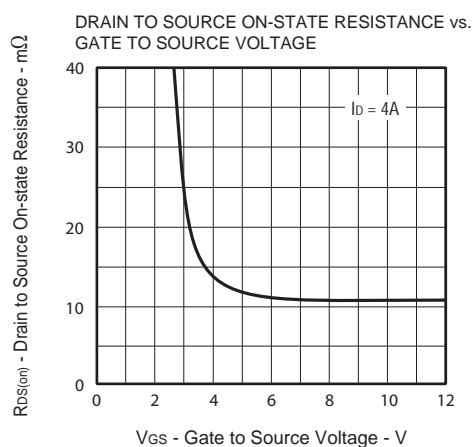
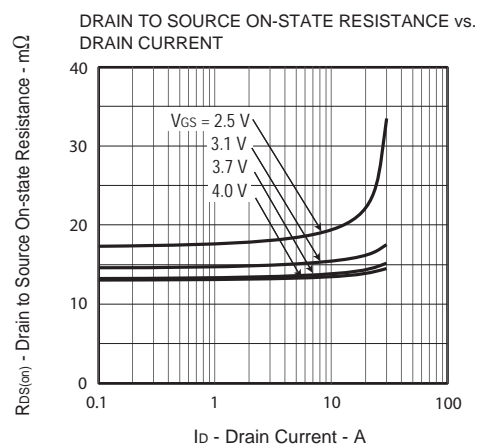
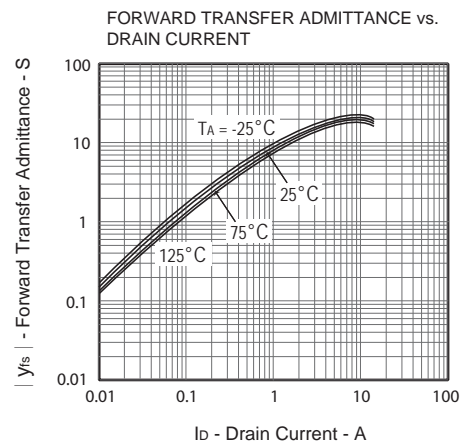
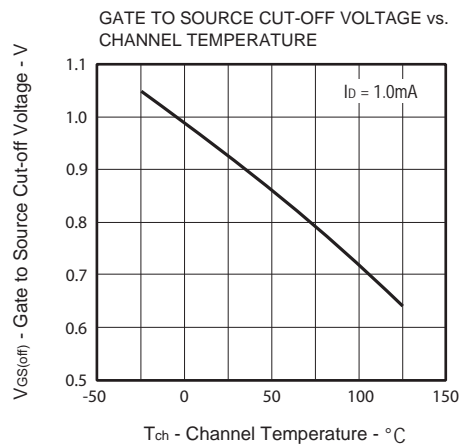
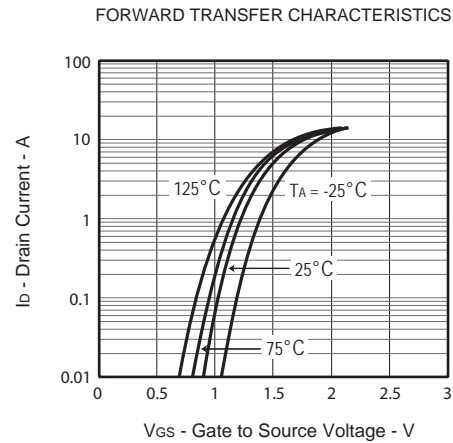
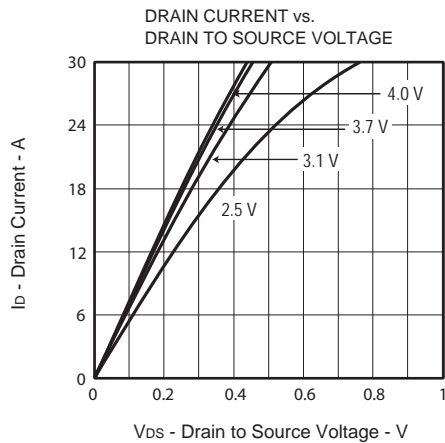
Ver 1.0

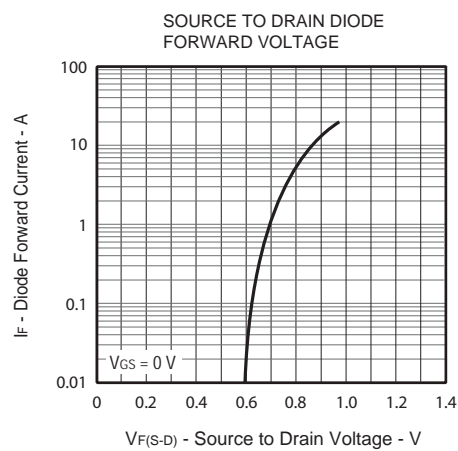
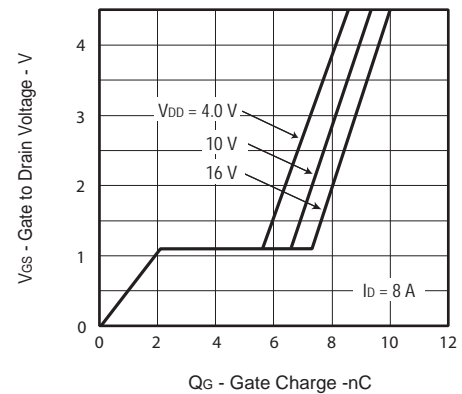
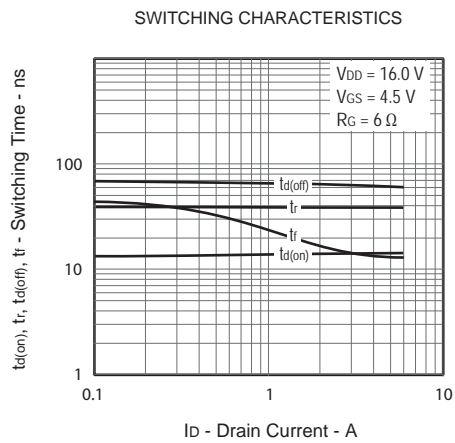
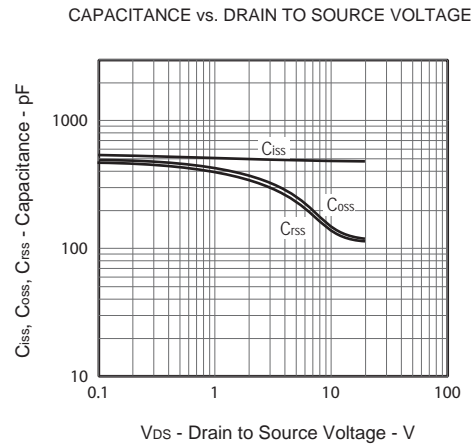
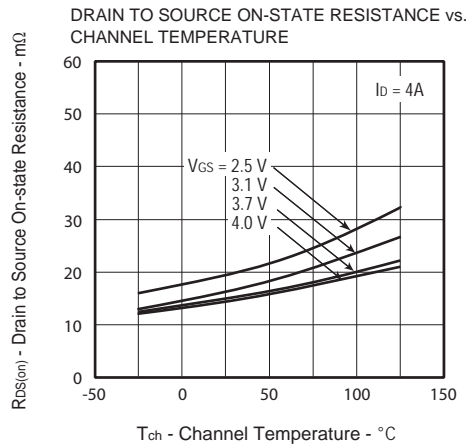
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±12V , V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =1mA	0.5	1	1.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =4.5V , I _D =4A	10.5	12.5	14.5	m ohm
		V _{GS} =4.0V , I _D =4A	11	13	15	m ohm
		V _{GS} =3.7V , I _D =4A	12	13.5	15.5	m ohm
		V _{GS} =3.1V , I _D =4A	13	15	18	m ohm
		V _{GS} =2.5V , I _D =4A	14.5	18	22	m ohm
g _{FS}	Forward Transconductance	V _{DS} =5V , I _D =4A		20		S
DYNAMIC CHARACTERISTICS [°]						
C _{iss}	Input Capacitance	V _{DS} =10V,V _{GS} =0V f=1.0MHz		481		pF
C _{OSS}	Output Capacitance			164		pF
C _{RSS}	Reverse Transfer Capacitance			150		pF
SWITCHING CHARACTERISTICS [°]						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =16V I _D =4A V _{GS} =4.5V R _{GEN} = 6 ohm		16		ns
t _r	Rise Time			50		ns
t _{D(OFF)}	Turn-Off Delay Time			42		ns
t _f	Fall Time			31		ns
Q _g	Total Gate Charge	V _{DS} =16V,I _D =8A, V _{GS} =4.5V		10		nC
Q _{gs}	Gate-Source Charge			2.1		nC
Q _{gd}	Gate-Drain Charge			5.2		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =4A		0.79	1.2	V
Notes						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width < 10us, Duty Cycle < 1%.						
c.Guaranteed by design, not subject to production testing.						

Mar,09,2012

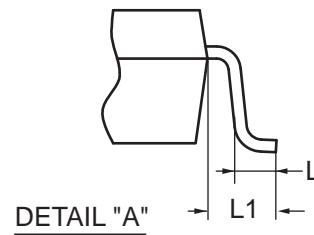
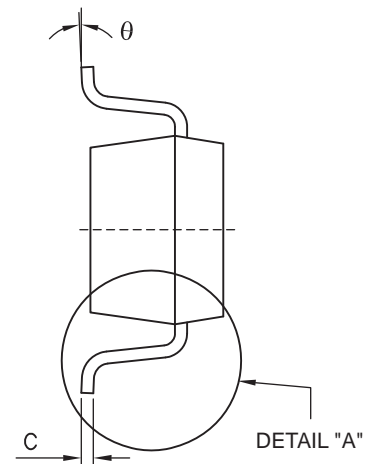
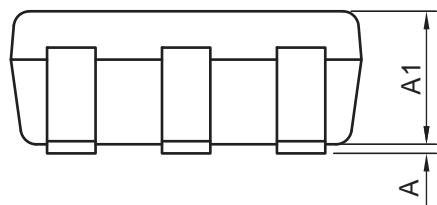
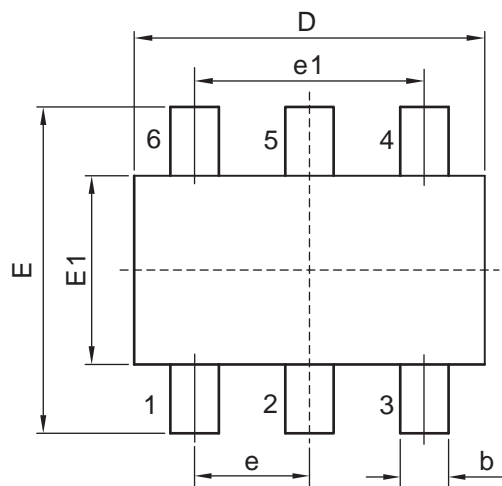






PACKAGE OUTLINE DIMENSIONS

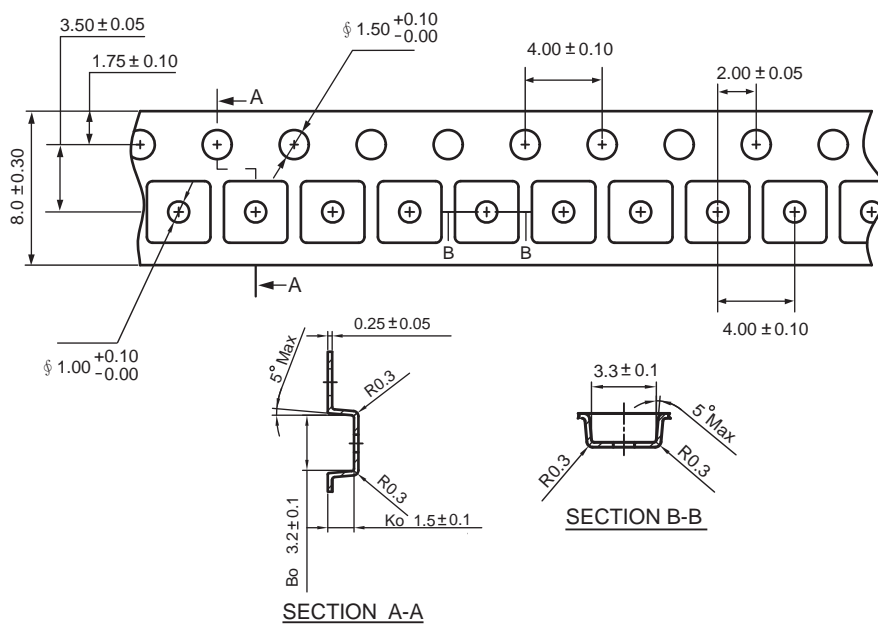
TSOT 26



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
D	2.692	3.099	0.106	0.122
E	2.591	3.000	0.102	0.118
E1	1.397	1.803	0.055	0.071
e	0.950 REF.		0.037 REF.	
e1	1.900 REF.		0.075 REF.	
b	0.300	0.500	0.012	0.020
C	0.080	0.200	0.003	0.008
A	0.000	0.100	0.000	0.004
A1	0.700	0.800	0.028	0.032
L	0.300	0.600	0.012	0.024
L1	0.600 REF.		0.023 REF.	
θ	0°	6°	0°	6°

TSOT 26 Tape and Reel Data

TSOT 26 Carrier Tape



TSOT 26 Reel

